



Faculty of Manufacturing Engineering

**SYNTHESIS AND CHARACTERIZATION OF
ELECTRODEPOSITED NICKEL CHALCOGENIDES FOR
PHOTOELECTROCHEMICAL / SOLAR CELL
APPLICATION**

Rajes a/p K.M.Rajan

Master of Science in Manufacturing Engineering

2014

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CHALCOGENIDES FOR PHOTOELECTROCHEMICAL / SOLAR CELL APPLICATION**

RAJES A/P K.M.RAJAN

**A thesis submitted
in fulfillment of the requirements for the degree of Master of Science
in Manufacturing Engineering**

Faculty of Manufacturing Engineering

UNIVERSITI TEKNIKAL MALAYSIA MELAKA

2014

DECLARATION

I declare that this thesis entitled “Synthesis and Characterization of Electrodeposited Nickel Chalcogenides for Photoelectrochemical / Solar Cell Application” is the result of my own research except as cited in the references. The thesis has not been accepted for any degree and is not concurrently submitted in candidature of any other degree.

Signature :

Name :

Date :

APPROVAL

I hereby declare that I have read this thesis and in my opinion this thesis is sufficient in terms of scope and quality for the award of Master of Science in Manufacturing Engineering.

Signature :

Supervisor Name :

Date :

DEDICATION

To my beloved supervisor, family and friends.

A wonderful teacher, understood me so well,

Helped me up, whenever I fell.

Even when I made a big mistake,

You said, we learn, the more we make.

Family and friends always been there,

making sure I was o.k.

The one that helped me be,

the kind of person I am today.

A simple thank you can turn a negative into a positive,

I find a way to be thankful to all of you,

Thank you! *For being my blessings.*

-Marelisa Fabrega

ABSTRACT

Nickel chalcogenides, NiX_2 ($X=S, Se$) thin films were successfully electrodeposited on indium-tin-oxide (ITO)-coated glass substrates. The deposition time for the thin films were set at 10 minutes to 30 minutes with an interval of 5 minutes. The thin films were characterized for their structural, morphological and compositional characteristics. Their optical and semiconducting parameters were also analyzed in order to determine the suitability of the thin films for photoelectrochemical (PEC) / solar cell applications. Films were well adherent to the substrates and grew up to thickness of $\approx 1.5\mu m$. Structural analysis via X-Ray Diffraction (XRD) analysis reveals that films are polycrystalline with increasing intensity of XRD peaks in thicker films. Preferred orientation of (2 2 0) plane in NiS_2 and (2 1 1) plane in $NiSe_2$ was observed as the highest peak in spectrum. The surface morphology of the films determined by Scanning Electron Microscope (SEM) showed the growth of the films to be uniform and well covered for thinner films. However, at longer deposition times, the structure of the films start to break into grains (flakes) due to maximum grain stress point. Compositional analysis via Energy Dispersive X-ray (EDX) technique confirmed the presence of Ni, S, and Se elements in the films synthesized. The optical bandgap energy of the films fit into the range (1-3eV) for a PEC / solar cell materials and decreases as the deposition time of the films increases. Bandgap energy of 1.12 eV and 1.15 eV was obtained for NiS_2 and $NiSe_2$ films deposited at 30 minutes and 25 minutes, respectively. Results on the semiconductor parameters analysis of the films showed that the nature of the Mott-Schottky plots indicates that the films obtained are of p-type material. All values come in the range of many other transition metal chalcogenides and this has proven that NiX_2 ($X=S, Se$) thin films are capable as a solar / PEC cell material

ABSTRAK

Filem nipis Nikel Kalkogenida, $NiX_2(X=S,Se)$ berjaya dielektrodeposisikan pada substrat kaca yang bersalutkan indium-timah-oksida (ITO). Masa deposisi untuk filem-filem nipis telah ditetapkan pada 10 minit hingga 30 minit dengan selang masa 5 minit. Filem-filem nipis telah disintesis untuk menentukan ciri-ciri struktur, morfologi dan komposisi. Parameter optik dan semikonduktor juga dianalisis untuk menentukan kesesuaian filem nipis untuk aplikasi fotovolt (PEC)/ sel solar. Film nipis melekat pada substrat dengan baik dan ketebalan filem bertambah kepada $\approx 1.5\mu m$. Analisis struktur melalui pembelauan sinar-X (XRD) mendedahkan bahawa filem berpolihablur mempunyai peningkatan pada intensiti puncak pada filem yang tebal. Orientasi pilihan bagi filem NiS_2 adalah (2 2 0) manakala $NiSe_2$ adalah (2 1 1). Morfologi permukaan filem-filem ditentukan dengan mikroskop pengimbasan elektron (SEM) dan ia diperlihatkan bahawa film dideposisikan dengan seragam dan juga meliputi seluruh permukaan substrat dengan film nipis. Walau bagaimanapun, pada masa deposisi yang lebih panjang, struktur filem-filem mula berpecah dan berbentuk kepingan. Analisis komposisi filem melalui teknik tenaga serakan sinar-X (EDX) mengesahkan kehadiran elemen-elemen Ni, S, dan Se dalam filem-filem yang disintesis. Nilai jurang tenaga optik perlu berada dalam julat (1-3eV) untuk aplikasi fotovolt /sel solar dan nilai tersebut akan berkurangan dengan masa deposisi filem yang bertambah. Nilai jurang tenaga sebanyak 1.12 eV dan 1.15 eV telah diperolehi bagi filem NiS_2 dan $NiSe_2$ yang dideposisi pada 30minit dan 25minit. Dapatan daripada analisis parameter semikonduktor melalui plot Mott-Schottky menunjukkan bahawa filem- filem adalah daripada semikonduktor jenis-p. Semua nilai yang diperolehi adalah serupa dengan bahan kalkogenida logam peralihan yang lain dan ini telah membuktikan bahawa $NiX_2(X=S,Se)$ filem nipis mampu berfungsi sebagai bahan PEC/ sel solar

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TABLE OF CONTENTS

	PAGE
DECLARATION	
DEDICATION	
ABSTRACT	i
ABSTRAK	ii
ACKNOWLEDGEMENTS	iii
TABLE OF CONTENTS	iv
LIST OF TABLES	vi
LIST OF FIGURES	vii
LIST OF APPENDICES	ix
LIST OF ABBREVIATIONS AND SYMBOLS	x
LIST OF PUBLICATIONS	xii
CHAPTER	
1. INTRODUCTION	1
1.1 Background	1
1.2 Problem Statement	4
1.3 Research Objectives	6
1.4 Significance of the Research	6
1.5 Structure of the Thesis	7
2. LITERATURE REVIEW	8
2.1 Introduction	8
2.2 Energy Resources	8
2.2.1 Solar Energy	10
2.3 Photoelectrochemical Solar Cell (PEC) Application	11
2.3.1 PEC Mechanism	13
2.4 Semiconductor Compounds and Alloys	13
2.4.1 Transition Metal Chalcogenide Compounds	13
2.5 Thin Film Technology	16
2.6 Thin Film Preparation Method	18
2.6.1 Electrodeposition Method	19
2.6.2 Cyclic Voltammetry (CV) Study	21
2.6.3 Kinetic Growth of Thin Film-Electrochemistry	22
2.6.4 'Ion-by-ion' Growth Mechanism	23
2.7 Properties of Electrodeposited Thin Film	24
2.7.1 Structural Properties	24
2.7.2 Surface Morphology Properties	27
2.7.3 Optical Properties	27
2.7.4 Electrical Semiconductor Parameters	30
2.8 Summary	33

3.	EXPERIMENTAL PROCEDURES	35
3.1	Introduction	35
3.2	Substrate Preparation	37
3.3	Electrolyte Preparation as NiX ₂ (X= S,Se) Films Precursors	37
3.4	Thin Films Synthesis via Electrodeposition	38
	3.4.1 Cyclic Voltammetry Measurement	38
	3.4.2 Electrodeposition of NiX ₂ (X=S,Se) Thin Films	39
3.5	Characterization of Electrodeposited Thin Films	39
	3.5.1 Thickness of Electrodeposited Thin Films	39
	3.5.2 X-Ray Diffraction (XRD) Analysis	40
	3.5.3 Scanning Electron Microscopy (SEM)	41
	3.5.4 Energy Dispersive X-Ray (EDX) Analysis	41
3.6	Optical Properties of Electrodeposited Thin Films	41
3.7	Mott-Schottky Analysis of Electrodeposited Thin Films	42
3.8	Summary	42
4.	RESULTS AND DISCUSSION	43
4.1	Thin Films Synthesis via Electrodeposition	43
	4.1.1 Cyclic Voltammetry Measurements	43
4.2	Characterization of Electrodeposited Thin Films	46
	4.2.1 Thickness of Electrodeposited NiS ₂ and NiSe ₂ Thin Films	46
	4.2.2 Structural Analysis of Electrodeposited NiS ₂ and NiSe ₂ Thin Films	48
	4.2.3 Surface Morphology Studies of Electrodeposited NiS ₂ and NiSe ₂ Thin Films	54
	4.2.4 Compositional Analysis of Electrodeposited NiS ₂ and NiSe ₂ Thin Films	57
4.3	Optical Properties of Electrodeposited NiS ₂ and NiSe ₂ Thin Films	61
4.4	Semiconductor Parameters of Electrodeposited NiS ₂ and NiSe ₂ Thin Films	65
4.5	Summary	70
5.	CONCLUSIONS AND RECOMMENDATIONS	72
5.1	Conclusions	72
5.2	Recommendations for Further Studies	73
	REFERENCES	74
	APPENDICES	94

LIST OF TABLES

TABLE	TITLE	PAGE
2.1	Type of transition and plot drawn.	29
3.1	Bath composition for NiX ₂ (X=S,Se) electrodeposition with bath condition of pH ~10 and temperature 40±2°C.	38
4.1	Thickness of NiS ₂ and NiSe ₂ thin films with different deposition times.	47
4.2	Comparison of experimental 'd' values with JCPDS data for NiS ₂ thin films.	50
4.3	Comparison of experimental 'd' values with JCPDS data for NiSe ₂ thin films.	52
4.4	Elemental composition of Ni ₃ S thin films.	60
4.5	Elemental composition of Ni ₃ Se thin films.	61
4.6	Bandgap energy values corresponding to film thickness of NiS ₂ and NiSe ₂ thin films.	65
4.7	Summary of the results obtained from the Mott-Schottky plots for NiS ₂ films.	67
4.8	Summary of the results obtained from the Mott-Schottky plots for NiSe ₂ films.	68

LIST OF FIGURES

FIGURE	TITLE	PAGE
2.1	Projected annual global energy production, in exajoules per year.	10
2.2	U.S. electricity generation capacity 2012 vs. 2013.	11
2.3	Example of carrier generation under illumination arising at solid-semiconductor electrolyte interface (PEC).	13
2.4	Efficiency comparison of technology.	18
2.5	Schematic representation of the electrochemical cell for electrochemical Deposition of TMCs electrolyte.	20
2.6	Typical CV graph for electrolyte solution.	21
2.7(a)	Example of As_2S_3 thin film with amorphous nature.	25
2.7(b)	Example of PbS thin film with polycrystalline nature.	25
2.8(a)	Simple cubic structure	26
	(b) orthorhombic structure	26
2.9 (a)	Example of direct bandgap semiconductors such as GaAs, InP and GaN.	29
2.9(b)	Example of indirect bandgap semiconductor such as Si and Ge.	29
2.10(a)	Example of Mott-Schottky plot of p-type $CuInSe_2$ thin film.	30
2.10(b)	Example of Mott-Schottky plot of n-type selenium thin films modified with lead atoms.	30
2.11	Electric flows in p-n junction for solar application.	32
3.1	Flow of study in preparation and characterization of NiX_2 (X=S,Se) thin films.	36
3.2	A three-electrode cell system used in electrodeposition setup.	39
4.1	Cyclic voltammogram of the electrodes using glass substrates in $NiSO_4 \cdot 6H_2O + Na_2S_2O_3$ solution	44
4.2	Cyclic voltammogram of the electrodes using glass substrates in $NiSO_4 \cdot 6H_2O + Na_2Se_2O_3$ solution	45
4.3	(a) NiS_2 film in dark greyish color	46
	(b) $NiSe_2$ film in dark red color	46
4.4	Variation of thickness with deposition time for NiS_2 and $NiSe_2$ thin films Deposited on ITO-glass substrate	48
4.5	XRD pattern for NiS_2 thin films deposited at different deposition Times	50

4.6	XRD pattern for NiSe ₂ thin films deposited at different deposition times	52
4.7	Surface morphology of NiS ₂ thin films at different deposition times	55
4.8	Surface morphology of NiSe ₂ thin films at different deposition times	57
4.9	EDX spectrum of NiS ₂ thin film deposited at 30 minutes of deposition time.	59
4.10	EDX spectrum of NiSe ₂ thin film deposited at 30 minutes of deposition time.	60
4.11	Variation of NiS ₂ thin film deposited at different deposition times (a) $(\alpha h\nu)^2$ vs. $h\nu$ (b) bandgap vs. deposition time	62
4.12	Variation of NiSe ₂ thin film deposited at different deposition times (a) $(\alpha h\nu)^2$ vs. $h\nu$ and (b) bandgap vs. deposition time	63
4.13	Mott-Schottky plot for NiS ₂ thin film at different deposition times	66
4.14	Mott-Schottky plot for NiSe ₂ thin film at different deposition times.	67

LIST OF APPENDICES

APPENDIX	TITLE	PAGE
A	Molarity Calculation for NiX_2 (X= S,Se) Precursors	93
B	Thickness increase calculation NiX_2 (X= S,Se)	97
C(a)	Elemental ratio calculation for NiS_2	98
C(b)	Elemental ratio calculation for NiSe_2	99

LIST OF ABBREVIATIONS AND SYMBOLS

(i) Abbreviations

CVD	Chemical Vapour Deposition
CE	Counter Electrode
CIGS	Copper Indium Gallium Selenide
EDX	Energy Dispersive X-Ray
E_g	Energy gap
FWHM	Full width at half maximum
ITO	Indium-Tin-Oxide
LCR	Inductance-Capacitance-Resistance
N	Doping density
N_A	Acceptor impurities density
N_c	Density of states in conduction band
PEC	Photoelectrochemical
PV	Photovoltaics
PVD	Physical Vapour Deposition
RE	Reference Electrode
SCE	Saturated Calomel Electrode
SEM	Scanning Electron Microscope
TMC	Transition Metal Chalcogenide
UV-Vis	Ultraviolet-Visible
V_b	Band bending
V_{fb}	Flat band potential
WE	Working Electrode

(ii) Symbols

ϵ Dielectric constant

α photon energy

λ wavelength of X-Ray

β Full width half maximum

θ Bragg's angle

LIST OF PUBLICATIONS

(i) Conference

Parts of this thesis have been presented in:

Rajes a/p K.M.Rajan, Mohd. Zaidan A.Z., and T.Joseph Sahaya Anand.,2012. Electrosynthesized NiS₂ Thin Films and Their Characterization Studies.Presented at : The International Conference on Design and Concurrent Engineering (iDECON 2012), 15-16 October 2012, Melaka.

(ii) Journal

Parts of this thesis have been published in:

(a) Joseph Sahaya Anand, **Rajes K.M Rajan** and Abdul Aziz Mohd Zaidan, 2013. Electrosynthesized NiS₂ Thin Films and Their Optical and Semiconductor Studies. *Reports in Electrochemistry*, 3, pp. 25-29.

(b) T. Joseph Sahaya Anand and **Rajes K.M. Rajan**, 2014. Synthesis and Characterization of Electrodeposited NiX₂(X=S,Se) Thin Films for Solar Energy Conversion. *Materials and Manufacturing Processes* (under revision).

(c) T. Joseph Sahaya Anand and **Rajes K.M. Rajan**, 2014. Characterization of the Surface Properties of NiSe₂ Thin Films: Influence of Deposition Time. *Thin Solid Films* (Submitted).

(d) Joseph Sahaya Anand, Mohd Zaidan Abdul Aziz, Shariza Sharir, **Rajes K.M.Rajan**, Chua, 2014. Electrochemical Studies of NiSe₂ Thin Films: Growth and Analysis of TEA and EDTA Additives. *Thermochemica Acta* (Submitted).

CHAPTER 1

INTRODUCTION

1.1 Background

Growing fuel prices and fast depleting conventional energy source has led to findings on sustainable and efficient energy source. Hence, renewable energy has been suggested as a viable approach for this particular energy crisis. Presently, many research group has focused on solar energy as the most promising renewable energy to cater the future energy demand due to its abundancy and inexhaustibility (Hennayaka and Lee, 2013).

Photoelectrochemical (PEC) is a solar device which is fabricated with semiconductor electrolyte interface. Being an advanced microelectronic technology, PEC can be applied for electrochemical energy conversion and energy storage (Yadav and Masumdar, 2010). At present, the mainstream of solar technology is based on crystalline silicon (c-Si) wafers (Aberle, 2009). The c-Si wafers require large amount of materials for the PEC fabrication. Thus, the c-Si wafers are extremely expensive for large scale production (Anuar *et al.*, 2007). Prior to the high material consumption and high cost in wafer technology, researchers have focused on other possible alternative technology and materials to develop solar device (Moheimani and Parlevliet, 2013).

Concurrently, thin film technology has been introduced as the cutting edge in developing a solar device. Thin-film is a successive thin layers, in thickness of 1 μ m to 4 μ m deposited onto a substrate such as glass, polymer, or metal (Gangopadhyay *et al.*, 2013). This technology significantly use less material than bulk crystalline solar cells. This makes the thin film technology more efficient in terms of material consumption (Moheimani and

Parlevliet, 2013). Hence, thin film technology can be considered as an engineering breakthrough in solar technology.

Research is being carried out extensively in finding new materials for energy conversion for reasonable cost by not compromising their efficiency (Duchatelet *et al.*, 2013). For energy conversion, the most suitable band gap energy is about 1.0-1.6eV. However, not all semiconductor materials are suitable for solar cells (Moheimani and Parlevliet, 2013). Owing to this efforts in finding new materials, Transition Metal Chalcogenides (TMC) are proposed as the most satisfactory semiconductor materials for PEC application. TMC, is combinatorial of transition metal and chalcogenide, MX_2 (M: Cd, Mo, Zn; X: S, Se and Te). TMC possesses excellent optical, electrical and semiconductor properties, especially in the thin film form (Anand and Shariza, 2012). Hence, TMC materials are under limelight for PEC fabrication by adopting thin film technology. At present, Cadmium Telluride, CdTe is the most ideal TMC material for thin film with its narrow and direct band gap $\sim 1.5\text{eV}$ (Yang *et al.*, 2010). Apart from CdTe, Cadmium Sulphide, CdS (Yadav and Masumdar, 2011), Cadmium Selenide, CdSe (Hankare *et al.*, 2011), Zinc Sulphide, ZnS (Luque *et al.*, 2013), and Tin Sulphide, SnS (Jain and Arun, 2013) thin films are also developed for PEC application. It is evident that cadmium chalcogenides are the most widely used TMC material for energy conversion purpose due to its significant photoconversion efficiency (Hankare *et al.*, 2003). However, Cd is very toxicative and harmful to the environment (Aberle, 2009).

Correspondingly, in a recent study, Nickel has been found to be potential candidate to substitute Cadmium in thin film chalcogenide as a material with better electrical properties to meet solar cell expectations. According to the investigation, Ni^{2+} has a standard ionic radius of 0.069nm, which is slightly less than Cd^{2+} (0.097nm) and higher electronegativity of 1.91 Pauling compared to Cd^{2+} (1.61 Pauling) (Rmili *et al.*, 2013).

Hence, with smaller ionic radius, nickel chalcogenides could form stronger ionic bonds with higher electronegativity that makes it attracts electrons effectively. Apart from this, nickel transition metal has longer life time with better functionality due its physical properties of high melting point 1453°C and high anti corrosive and resistivity. Ultimately, nickel is also >60% recyclable. Thus, it contributes to longer product cycle and prevents source depletion (Mistry, 2012). On the other hand, the chalcogens sulphide and selenium (X=S,Se), are non-metal while Tellurium (Te) is a metalloid in an alkaline. Hence, chemical behavior and reaction of sulphide and selenium are reported similar which are in contrast to Telluride (Mathur *et al.*, 1995). In this regard, NiX₂(X=S,Se) films were investigated for a comprehensive study of their suitability for PEC application.

Nickel chalcogenides can be synthesized by spray pyrolysis, electrochemical deposition and sputtering (Yadav and Masumdar, 2010a) (Kokate *et al.*, 2006) (Volobujeva *et al.*, 2009). One of the most attractive methods for producing nickel chalcogenide thin film, owing to the possibility of large area deposition at low cost is the potentiostate electrodeposition method. This method is relatively accurate and yields good quality films due to the potential reduction at the working electrode (Yang *et al.*, 2010). Correspondingly, it requires presence of reagents that act as a source of chalcogenide and complexation of metal ions that forms via 'ion-by-ion' growth mechanism (Hankare *et al.*, 2010).

This research work aims on NiX₂(X=S,Se) thin film and the studies include the observations on growth kinetics, structural, morphological, compositional, optical and semiconducting parameters. This film is expected to contribute on the advantageous and limitations stated in synthesizing the transition metal chalcogenide thin films, without compromising its functionality and properties.

1.2 Problem Statement

Fossil fuels are non-renewable. This resource is limited and expected to deplete by 2046. This indicates that in the year 2046, there will be almost no liquid fuel (Moheimani and Parlevliet, 2013). On the other hand, the world energy consumption is reported increasing at 10 Terawatts (TW) annually and by 2050 it is projected to be about 30 TW (Razykov *et al.*, 2011). Fossil fuels are depleting very fast and is becoming expensive day by day (Aloney *et al.*, 2009). Despite the fact expensive, fossil fuel exploitation is also contributing in environmental pollution and climate change (Tseng *et al.*, 2012). Clearly, decline of fossil fuel resource is not able to support the increasing energy demand at the long run. Therefore, alternate renewable energy, namely solar energy has been suggested to meet the future energy demand (Tyagi *et al.*, 2013). Correspondingly, photoelectrochemical solar cell is gaining popularity in compliance to its usage in energy conversion and energy storage. Consequently, PEC is being fabricated and investigated largely in order to improve their performance in solar energy conversion efficiency (Yadav and Masumdar, 2011).

At current market scenario, crystalline silicon (c-Si) dominates solar cell application due to its higher efficiencies of 24.7% (Moheimani and Parlevliet, 2013). Prior to wafer technology, c-Si consumes large amount of materials (Parida *et al.*, 2011). High production cost of solar cell comprises the cost of materials, technology used and material consumption (Borja *et al.*, 2011). Hence, c-Si usage seemed to be impossible to achieve PV module production cost below \$1/W and temporarily restricts wafer technology in solar cell fabrication (Razykov *et al.*, 2011). Meanwhile, indium and gallium are expensive elements and therefore makes the popular Copper Indium Gallium Selenide (CIGS) solar device with efficiency 20.3% (Zhou *et al.*, 2013) costly and commercially limited (Rath *et al.*, 2012).

Another challenge in solar cell is employing a suitable fabrication method which cost effective and suitable for large scale production. Contemporarily, the fabrication method is expected to yield a high quality thin film for solar cell application (Kaupmees *et al.*, 2007). Prior to cost competition, many researchers are in the effort of replacing vacuum usage in the fabrication method with cost efficient fabrication method (Todorov *et al.*, 2011). This is also supported by Kim *et al.*, (2005) claiming that the adopted fabrication method must be cost effective without compromising its efficiency.

Several toxic substances applied in solar cells claimed to be toxicative to the environment during production process, namely Cadmium Sulphide, CdS(Zhou *et al.*, 2011) (Lekiket and Aida., 2013). Hence, it limits the use of CdS as photoelectrode material for solar cell (Patil and Singh, 2010). Prompted by environmental underlying issues, a clean and renewable alternative energy solution is imperatively needed to sustain energy supply in the long run (Bhaskar *et al.*, 2013).

In summary, a sustainable energy supply can be explored efficiently by resolving the limitations. Thus, more thorough investigations should be made regarding solar energy as a realistic measure to find sustainable and clean energy. It is important to note that, to the best of our knowledge, the first report on nickel chalcogenides (NiS and NiSe) thin film prepared via solution growth technique was published in 1986 (Pramanik and Biswas, 1986) and followed by several reports after nearly two decades (Zhuang *et al.*, 2005) (Anuar *et al.*, 2004). Thus, this investigation of NiX₂(X=S,Se) thin film is expected to provide feasible study to discover the suitability of the material for PEC application.

1.3 Research Objectives

Based on the problem statements, this research is designed to accomplish the following specific objectives :

- i) To synthesize stoichiometry NiX_2 ($\text{X}=\text{S},\text{Se}$) thin films via electrodeposition technique.
- ii) To characterize the thin films for their structural, morphological and compositional studies for various deposition time and potential.
- iii) To analyze the optical properties of these thin films by determination of energy band gap.
- iv) To analyze the film semiconductor parameters that influences the suitability for energy conversion application.

1.4 Significance of the Research

This research contributes to the efforts in finding new material for PEC application. Owing to the contribution, the present study incorporates analytical tools, namely, X-Ray Diffraction (XRD), Scanning Electron Microscopy (SEM), Optical and Mott-Schottky. The analytical tools were adopted to determine the possibility of structural, morphological, optical and semiconductor properties of NiX_2 ($\text{X}=\text{S},\text{Se}$) film to be used for solar energy conversion. Thus, the results are expected to reflect the suitability of NiX_2 ($\text{X}=\text{S},\text{Se}$) film to fulfill the requirements as efficient solar cell material

1.5 Structure of the Thesis

The current chapter 1 introduces the context of the research covering issues such as the background, objectives and significance in order to give an overview on this research.